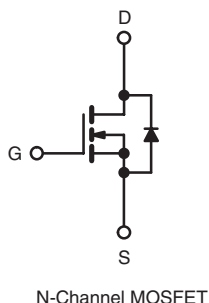
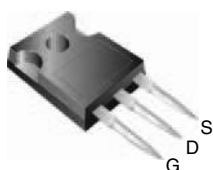


Power MOSFET

PRODUCT SUMMARY

V_{DS} (V)	600	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$	0.24
Q_g (Max.) (nC)	150	
Q_{gs} (nC)	45	
Q_{gd} (nC)	76	
Configuration	Single	

TO-247



FEATURES

- Hard Switching Primary or PFS Switch
- Low Gate Charge Q_g Results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Enhanced Body Diode dV/dt Capability
- Lead (Pb)-free Available



Available
RoHS*
COMPLIANT

BENEFITS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- High Speed Power Switching
- Motor Drive

ORDERING INFORMATION

Package	TO-247
Lead (Pb)-free	IRFP22N60KPbF
	SiHFP22N60K-E3
SnPb	IRFP22N60K
	SiHFP22N60K

ABSOLUTE MAXIMUM RATINGS $T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V _{DS}	600	V
Gate-Source Voltage			V _{GS}	± 30	
Continuous Drain Current	V _{GS} at 10 V	T _C = 25 °C	I _D	22	A
		T _C = 100 °C		14	
Pulsed Drain Current ^a			I _{DM}	88	
Linear Derating Factor				2.9	W/°C
Single Pulse Avalanche Energy ^b			E _{AS}	380	mJ
Repetitive Avalanche Current ^a			I _{AR}	22	A
Repetitive Avalanche Energy ^a			E _{AR}	37	mJ
Maximum Power Dissipation	T _C = 25 °C		P _D	370	W
Peak Diode Recovery dV/dt ^c			dV/dt	15	V/ns
Operating Junction and Storage Temperature Range			T _J , T _{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for 10 s			300 ^d	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting $T_J = 25\text{ }^\circ\text{C}$, $L = 1.5\text{ mH}$, $R_G = 25\text{ }\Omega$, $I_{AS} = 22\text{ A}$ (see fig. 12).
- $I_{SD} \leq 22\text{ A}$, $dI/dt \leq 360\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^\circ\text{C}$.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	40	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.24	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.34	

SPECIFICATIONS $T_J = 25\text{ °C}$, unless otherwise noted

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		600	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA ^d		-	0.30	-	V/°C
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		3.0	-	5.0	V
Gate-Source Leakage	I _{GSS}	V _{GS} = ± 30 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V		-	-	50	μA
		V _{DS} = 480 V, V _{GS} = 0 V, T _J = 125 °C		-	-	250	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 13 A ^b	-	0.240	0.280	Ω
Forward Transconductance	g _{fs}	V _{DS} = 50 V, I _D = 13 A ^b		11	-	-	S
Dynamic							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1.0 MHz, see fig. 5		-	3570	-	pF
Output Capacitance	C _{oss}			-	350	-	
Reverse Transfer Capacitance	C _{rss}			-	36	-	
Output Capacitance	C _{oss}	V _{GS} = 0 V	V _{DS} = 1.0 V , f = 1.0 MHz	-	4710	-	nC
			V _{DS} = 480 V , f = 1.0 MHz	-	92	-	
Effective Output Capacitance	C _{oss eff.}		V _{DS} = 0 V to 480 V	-	180	-	
Total Gate Charge	Q _g	V _{GS} = 10 V	I _D = 22 A, V _{DS} = 480 V see fig. 6 and 13 ^b	-	-	150	nC
Gate-Source Charge	Q _{gs}			-	-	45	
Gate-Drain Charge	Q _{gd}			-	-	76	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 300 V, I _D = 22 A, R _G = 6.2, V _{GS} = 10 V, see fig. 10 ^b		-	26	-	ns
Rise Time	t _r			-	99	-	
Turn-Off Delay Time	t _{d(off)}			-	48	-	
Fall Time	t _f			-	37	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	22	A
Pulsed Diode Forward Current ^a	I _{SM}			-	-	88	
Body Diode Voltage	V _{SD}	T _J = 25 °C, I _S = 22 A, V _{GS} = 0 V ^b		-	-	1.5	V
Body Diode Reverse Recovery Time	t _{rr}	T _J = 25 °C	I _F = 22 A, dI/dt = 100 A/μs ^b	-	590	890	ns
		T _J = 125 °C		-	670	1010	
Body Diode Reverse Recovery Charge	Q _{rr}	T _J = 25 °C		-	7.2	11	μC
		T _J = 1 25 °C		-	8.5	13	
Reverse Recovery Current	I _{RRM}	T _J = 25 °C		-	26	39	
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L _S and L _D)					

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.
c. $C_{oss\text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80 % V_{DS} .

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

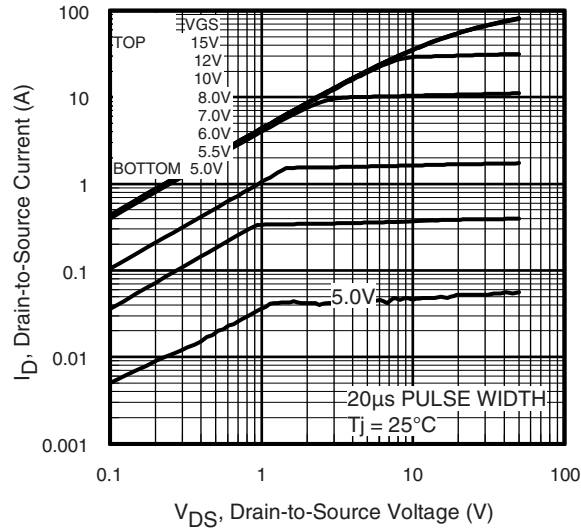


Fig. 1 - Typical Output Characteristics

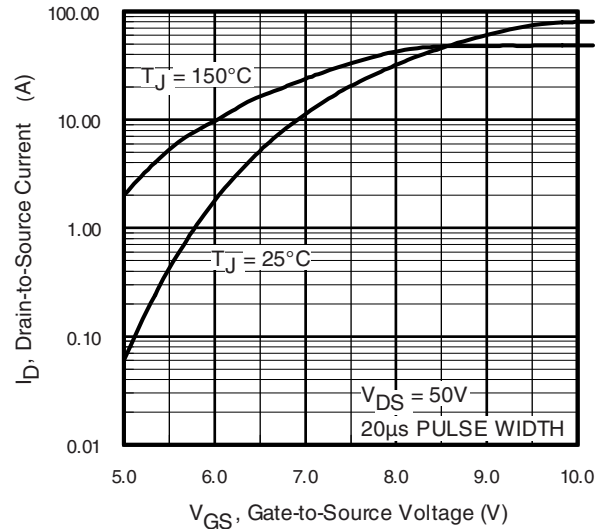


Fig. 3 - Typical Transfer Characteristics

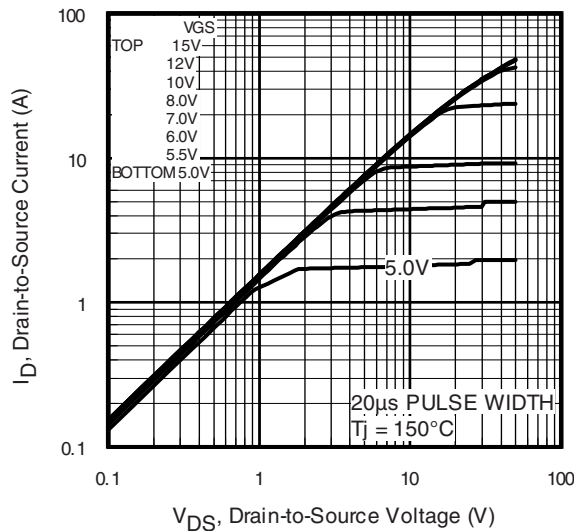


Fig. 2 - Typical Output Characteristics

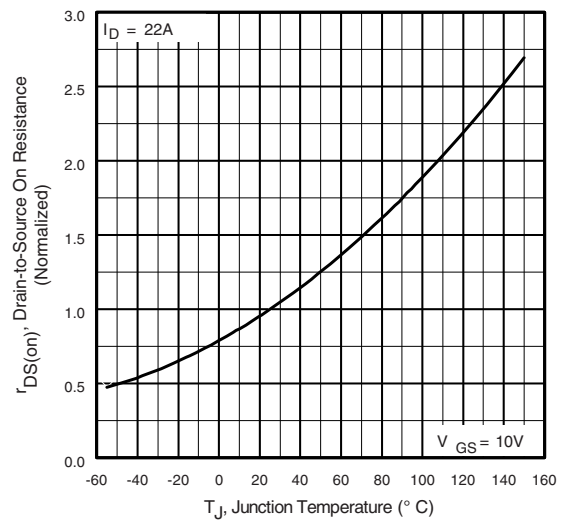


Fig. 4 - Normalized On-Resistance vs. Temperature

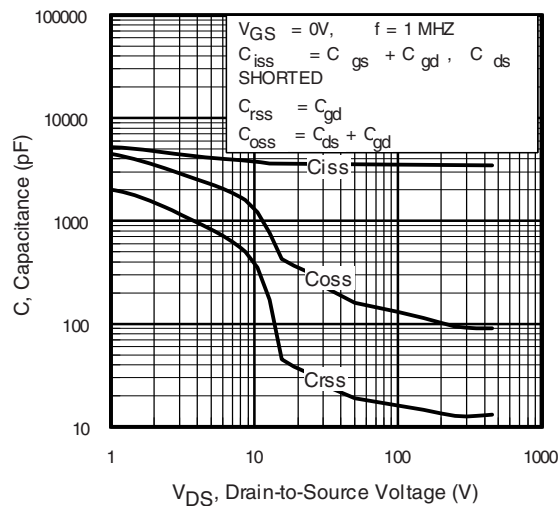


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

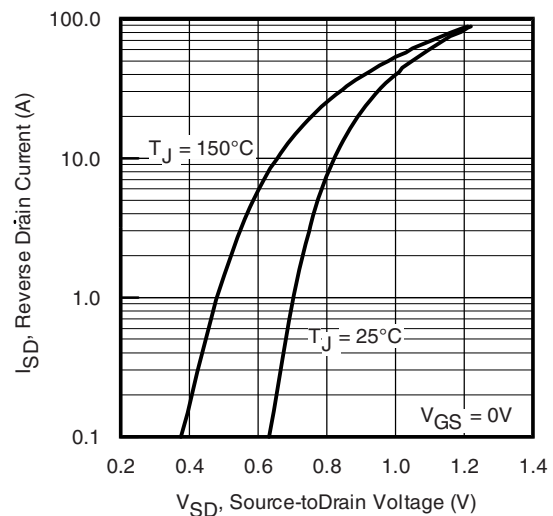


Fig. 7 - Typical Source-Drain Diode Forward Voltage

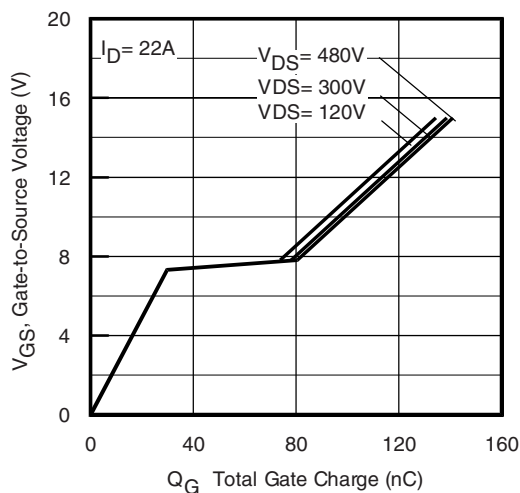


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

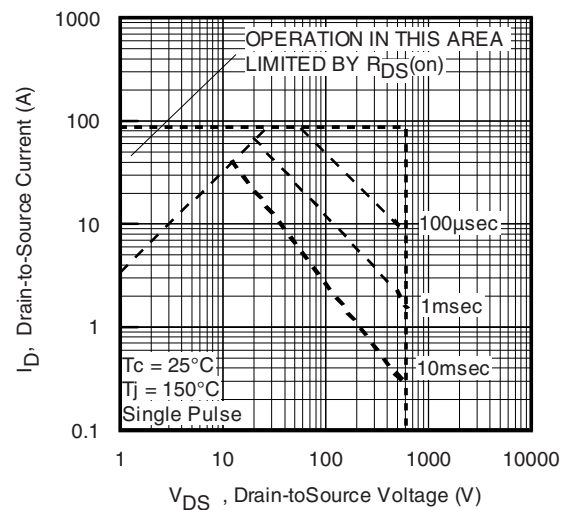


Fig. 8 - Maximum Safe Operating Area

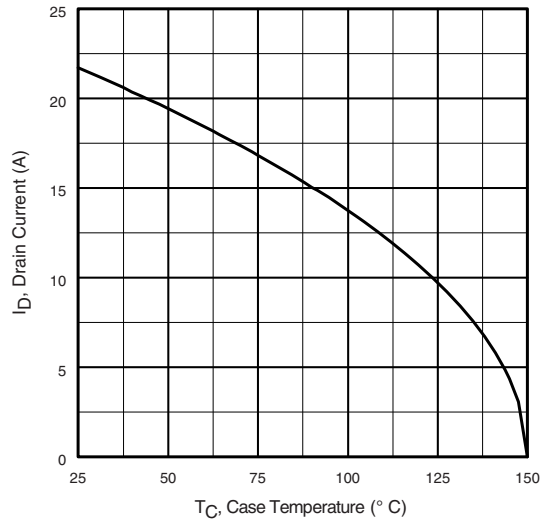


Fig. 9 - Maximum Drain Current vs. Case Temperature

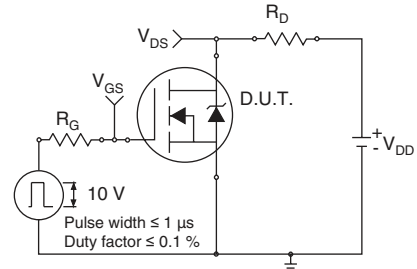


Fig. 10a - Switching Time Test Circuit

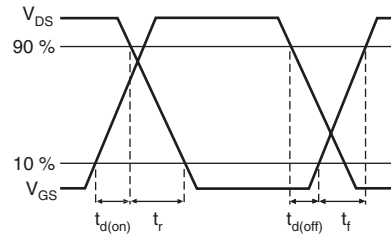


Fig. 10b - Switching Time Waveforms

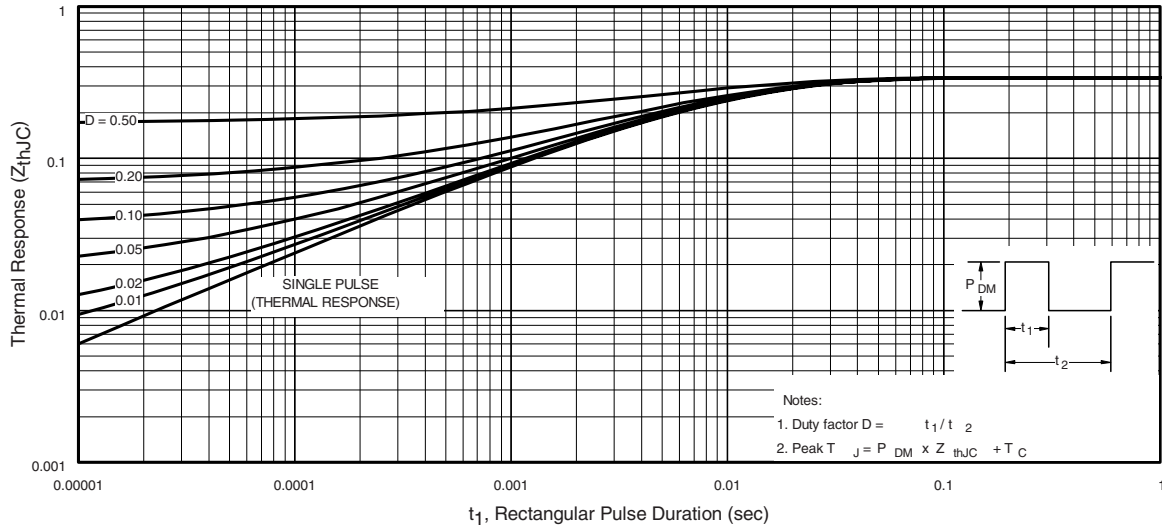


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

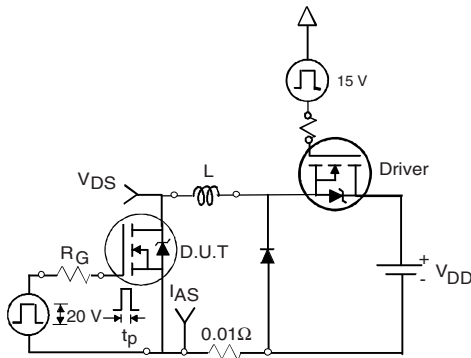


Fig. 12a - Unclamped Inductive Test Circuit

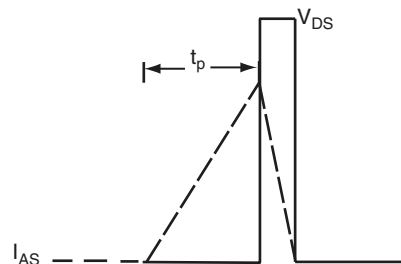


Fig. 12b - Unclamped Inductive Waveforms

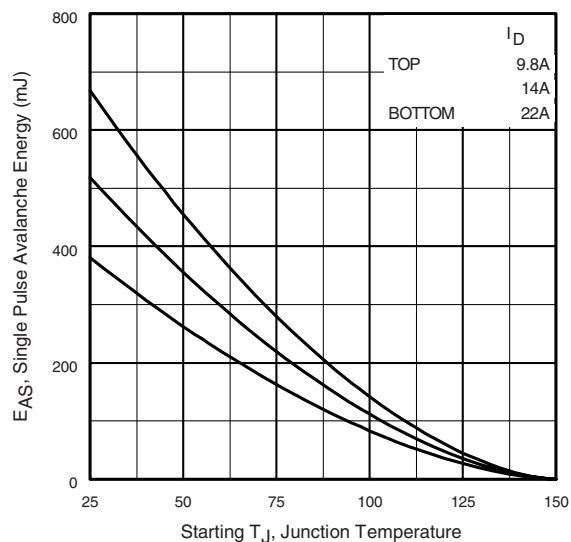


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

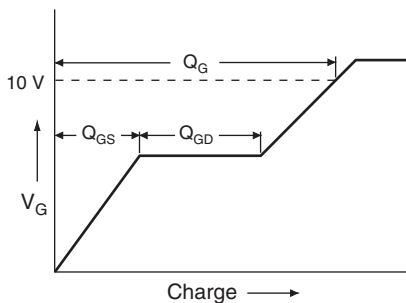


Fig. 13a - Basic Gate Charge Waveform

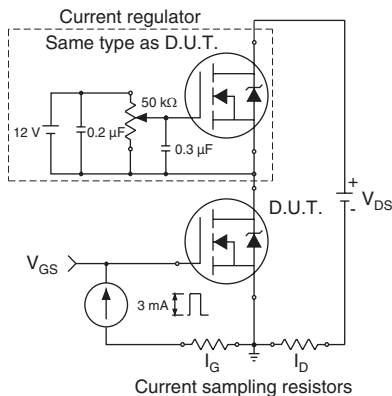


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit

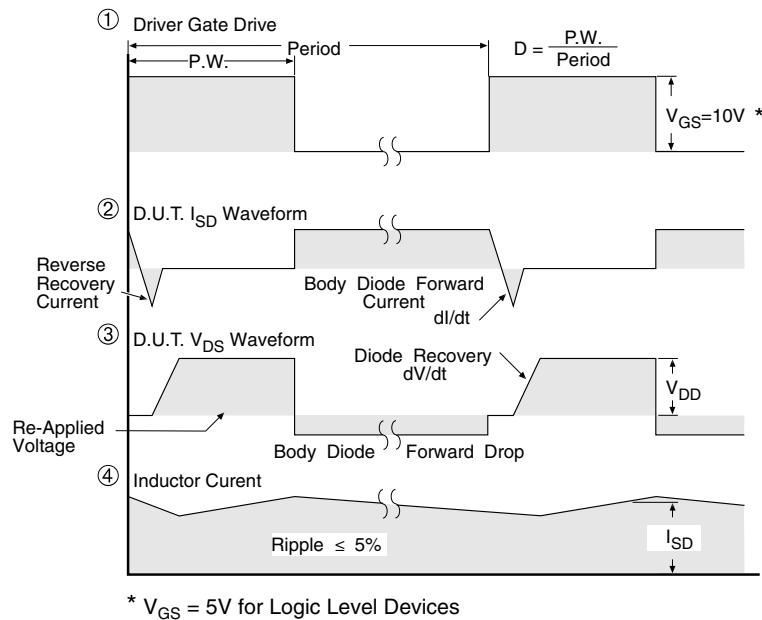
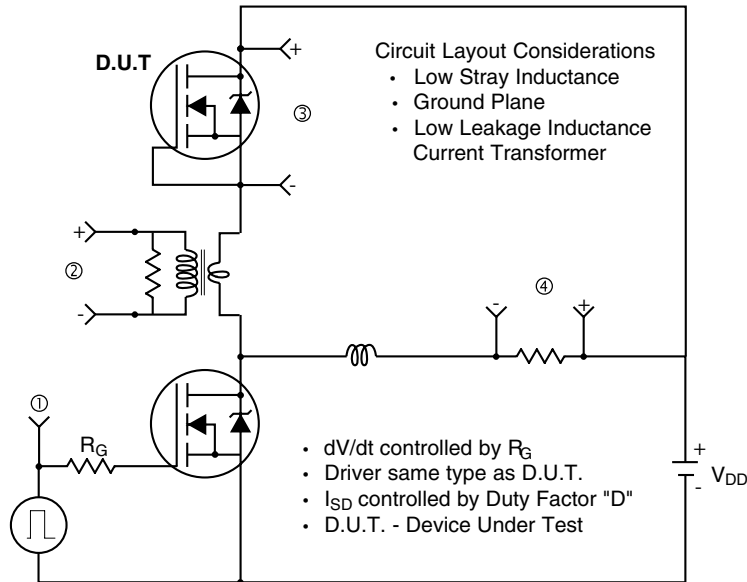


Fig. 14 - For N-Channel

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